HSK83

Silicon Epitaxial Planar Diode for High Voltage Switching

HITACHI

ADE-208-169B (Z)
Rev. 2

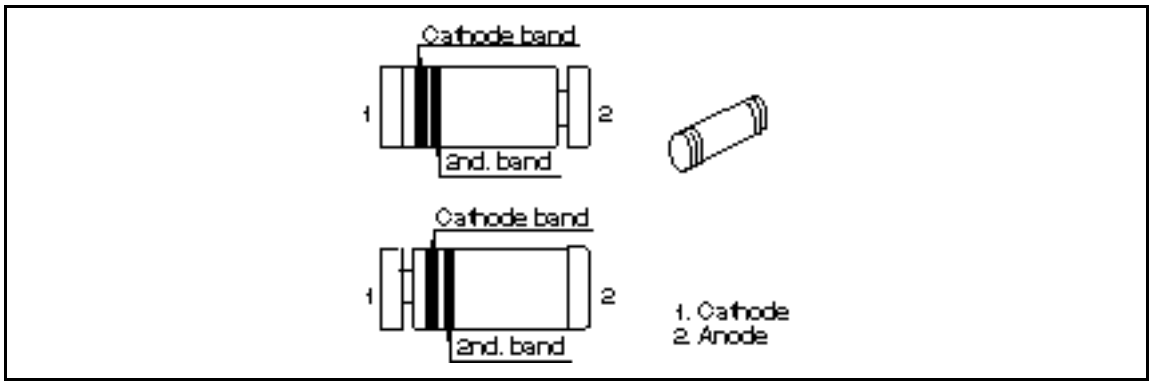
Features

- High reverse voltage. (V_R = 250V)
- LLD package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Cathode band	2nd.band	Package Code
HSK83	White	Verdure	LLD

Outline



Hitachi semiconductor

Absolute Maximum Ratings[*2] (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}[*1]	300	V
Reverse voltage	V_R	250	V
Peak forward current	I_{FM}	625	mA
Non-Repetitive peak forward surge current	I_{FSM}[*2]	1	A
Average forward current	I_o	150	mA
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	–65 to +175	°C

Notes: 1. Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.
2. Within 1s forward surge current.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	I_F = 100mA
Reverse current	I_{R1}	—	—	0.1	µA	V_R = 250V
	I_{R2}	—	—	100		V_R = 300V
Capacitance	C	—	—	3.0	pF	V_R = 0V, f = 1MHz
Reverse recovery time	t_{rr}	—	—	100	ns	I_F = I_R = 30mA, Irr = 3mA, R_L = 100Ω

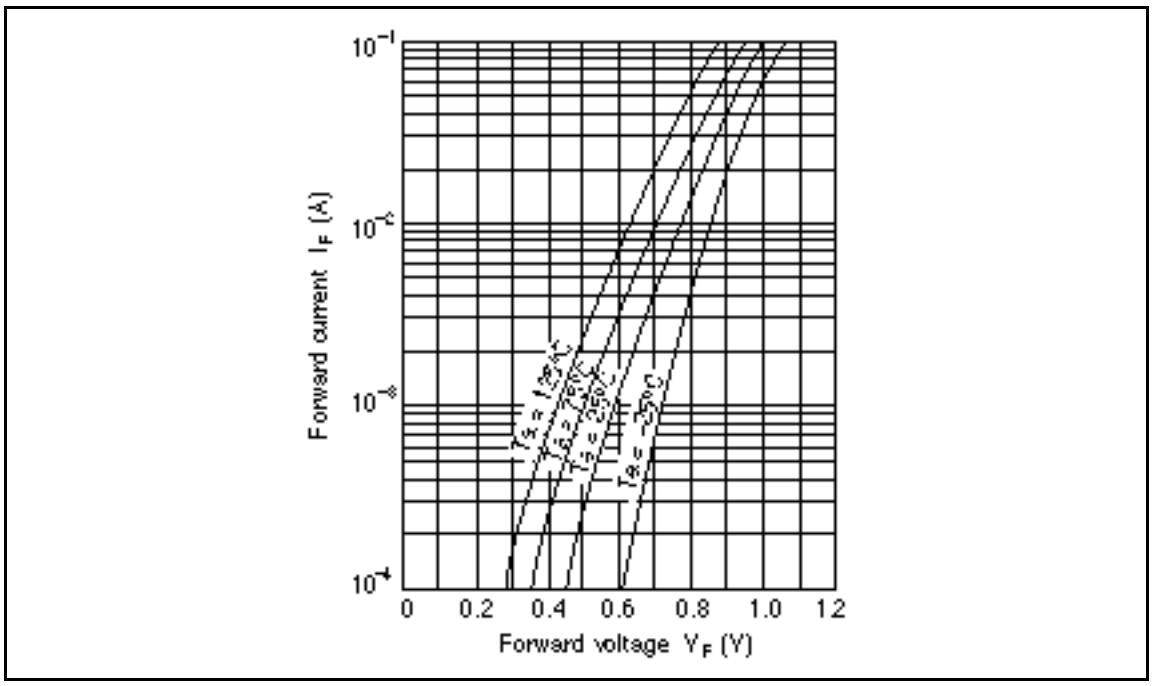


Fig.1 Forward current Vs. Forward voltage

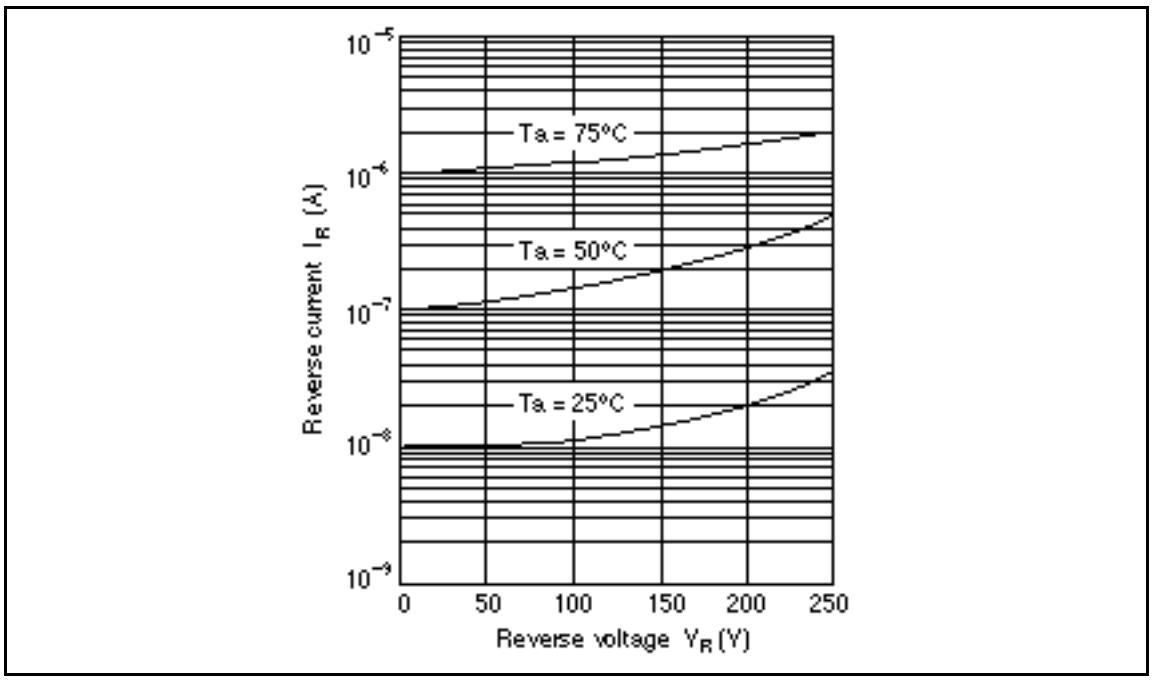


Fig.2 Reverse current Vs. Reverse voltage

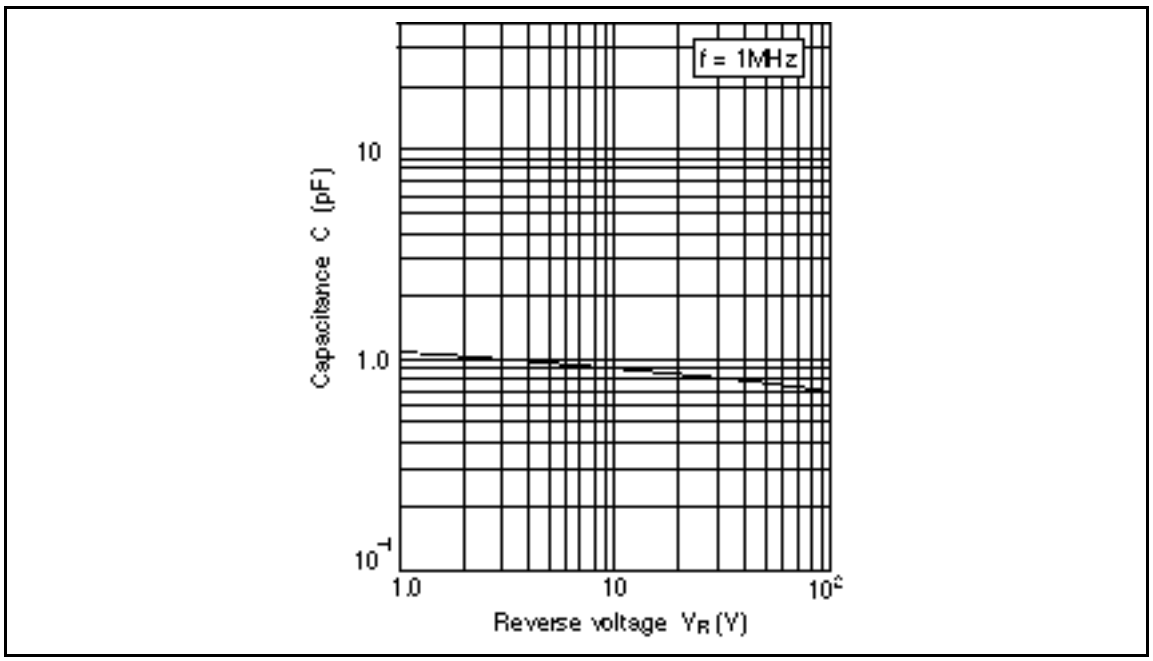
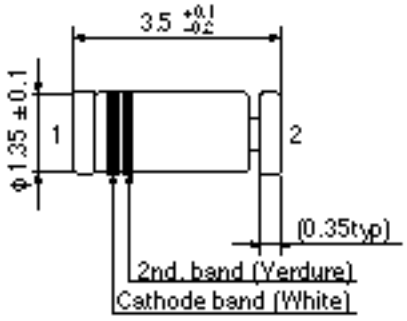
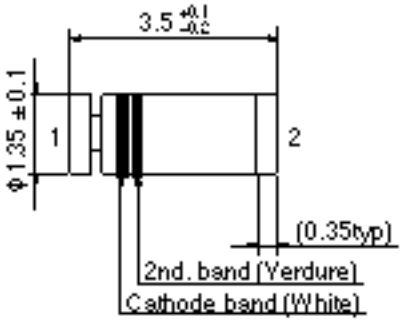


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm





1 Cathode
2 Anode

( ) : Reference only

HITACHI Code	LLD
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.027